PCN Number: 2017062800		8000			PCN Date:	June 29, 2017	
Title: Die Coat	itle: Die Coating change for Select Devices						
Customer Conta	omer Contact: PCN Manager Dept: Quality Services						
Proposed 1 st Ship Date:		Sent 29 2017		Estimated Sam		Date provided at	
Change Type	P	- opt _ o ,			Availability: sample request		
Change Type:						Rump Sito	
					Wafer Bump Material		
Assembly Materials			Part number change		Wafer Bump Process		
Mechanical Specification		<u>ר</u>			Wafer Fab Site		
Packing/Shipping/Labeling		ing			Wafer Fab Materials		
			_		Wafer F	ab Process	
			PCN	Details	· ·		
Description of C	hange:						
Texas Instruments is pleased to announce a change in the Die overcoat material for Select Devices listed in the "Product Affected" Section as follows:							
		Curren	t	Proposed			
Ľ		Die Overc	oat	No Die overcoat			
Reason for Change:							
Supplier no longer manufactures the die overcoat material used for these devices.							
Anticipated impa	act on Fo	rm, Fit, Fu	inction,	Quality or Relial	oility (positiv	e / negative):	
None							
Anticipated impa	act on Ma	terial Dec	laration	1			
No Impact to Material Decla	the Daration	Mater produ releas obtair mater this P	Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the <u>TI Eco-Info website</u> . There is no impact to the material meeting current regulatory compliance requirements with this PCN change.				
Changes to product identification resulting from this PCN:							
None							
Product Affected:							
INA117AM INA117BM INA117SM INA117SMQ					SMQ		

Qualification Report

INA117 TO-99 (LMC) Die Coat Removal

Approve Date 20-Jun-2017

Product Attributes

Attributes Qual Device: INA117SMQ		QBS Process Reference: REF02BU	QBS Process Reference: REF102CU	QBS Package Reference: INA117BM	
Assembly Site	MMT	MLA	MLA	MMT	
Package Family	TO-Can	SOIC	SOIC	ТО99	
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	n/a	
Wafer Fab SupplierSFAB		SFAB	SFAB	HFAB/TFAB	
Wafer Process	HU-BIP-4 (630G)	BIP460G10B	BIP630G10B	HU-BIP-4 (630G)	

- QBS: Qual By Similarity

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: INA117SMQ	QBS Process Reference: REF02BU	QBS Process Reference: REF102CU	QBS Package Reference: INA117BM
ED	Electrical Characterization	Per Datasheet Parameters	Pass	Pass	Pass	-
HBM	ESD - HBM	700 V	1/3/0	-	-	-
CDM	ESD - CDM	500 V	1/3/0	1/3/0	-	-
HTOL	Life Test, 125C	1000 Hours	3/226/0	-	1/77/0	3/231/0
HTSL	High Temp. Storage Bake, 150C	1000 Hours	-	-	1/77/0	-
тс	Temperature Cycle, -65/150C	500 Cycles	3/231/0	-	-	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com